

REMARKS

Claim Amendments

Claim 1 has been amended to recite a wafer having a surface, the wafer comprising a plurality of regions of dielectric and polysilicon semiconductor exposed at the surface of the wafer after chemical mechanical planarization, the semiconductor regions formed over a substrate, wherein the semiconductor regions have a total surface area that is less than or equal to a first fraction of a total surface area of the wafer and each of the semiconductor regions have a shortest surface dimension that is less than or equal to a first width, the first fraction and the first width ensuring that the surface of the wafer can attract enough water to wet sufficiently allowing removal of residual particles therefrom.

Claim 30 has been amended to recite a wafer having a surface, the wafer comprising means for attracting water to the surface of the wafer; and means for repelling water from the surface of the wafer comprising polysilicon regions above a substrate that have a combined surface area that is less than or equal to a first fraction of a surface area of the wafer, wherein each of the regions has a shortest surface dimension that is less than or equal to a first width, and the first fraction and the first width ensure that the surface of the wafer can attract enough water to wet sufficiently allowing removal of residual particles therefrom.

Claim 44 has been amended to recite a wafer having a surface, the wafer comprising a plurality of regions of polysilicon hydrophobic material and hydrophilic material exposed at the surface of the wafer after chemical mechanical planarization, wherein the regions of hydrophobic material are deposited over a substrate and have a total surface area that is less than or equal to a first fraction of a total surface area of the wafer, and each of the regions of hydrophobic material have a shortest surface dimension that is less than or equal to a first width, the first fraction and the first width ensuring that the surface of the wafer can attract enough water to wet sufficiently allowing removal of residual particles therefrom.

Support for all three of these amendments can be found in the specification at paragraphs [0025] and [0028].

New claims 57, 59, and 61 recite that the polysilicon is doped polysilicon, and new claims 58, 60, and 62 recited that the doped polysilicon is doped by depositing a dopant along with the polysilicon. Support for these claims is found in paragraphs [0025] through [0028].



CONCLUSION

Applicants appreciate Examiner Mai's willingness to discuss the application in a telephone conversation on July 16, 2003.

In view of these amendments and remarks, Applicants submit that this application is in condition for allowance. **If any objections or rejections remain, Applicants respectfully request an interview to discuss the references.** In such event, the Examiner is asked to contact the undersigned agent at (408) 869-2921.

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Date

Pamela J. Squyres
Agent for Applicants
Reg. No. 52246

Pamela J. Squyres
Matrix Semiconductor
3230 Scott Blvd
Santa Clara, CA 95054
Tel. 408-869-2921